US00D775593S

(12) **United States Design Patent**
Edenharter et al.

(10) **Patent No.: US D775,593 S**
(45) **Date of Patent: ** Jan. 3, 2017**

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(54) **POWER SEMICONDUCTOR MODULE**

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(**) Term: **14 Years**

(21) Appl. No.: **29/517,908**

(22) Filed: **Feb. 18, 2015**

(30) **Foreign Application Priority Data**

Aug. 19, 2014 (EM) 002521518-0001

(51) **LOC (10) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/110, 182; 257/678, 684, 690, 691; 361/679.01, 713, 728, 736, 760, 761, 772, 361/775, 783, 820; 174/250, 253; 438/15, 438/25, 26, 51, 55, 63, 64, 106
CPC .. H01L 21/00; H01L 2224/42; H01L 2224/43; H01L 2021/00; H01L 2021/02; H01L 2021/04; H01L 21/4814; H01L 21/4846; H01L 21/4871; H01L 21/67144; H01L 23/12; H01L 23/13; H01L 23/14; H01L 23/147; H01L 2924/171; H01L 2924/1711; H01L 2924/1715; H01L 2924/17151; H01L 2924/181; H01L 2924/1811; H01L 2924/1815; H01L 2924/19042; H01L 2224/08054; H01L 23/58; H05B 41/14; H02B 6/4201; G02B 6/4256; G02B 6/4257; G02B 6/4261; G02B 6/4262; G02B 6/428; G02B 6/4281;H05K 1/14; H05K 1/141; H05K 1/142; H05K 1/144; H05K 1/18; H05K 1/181; H05K 1/182; H05K 1/026
See application file for complete search history.

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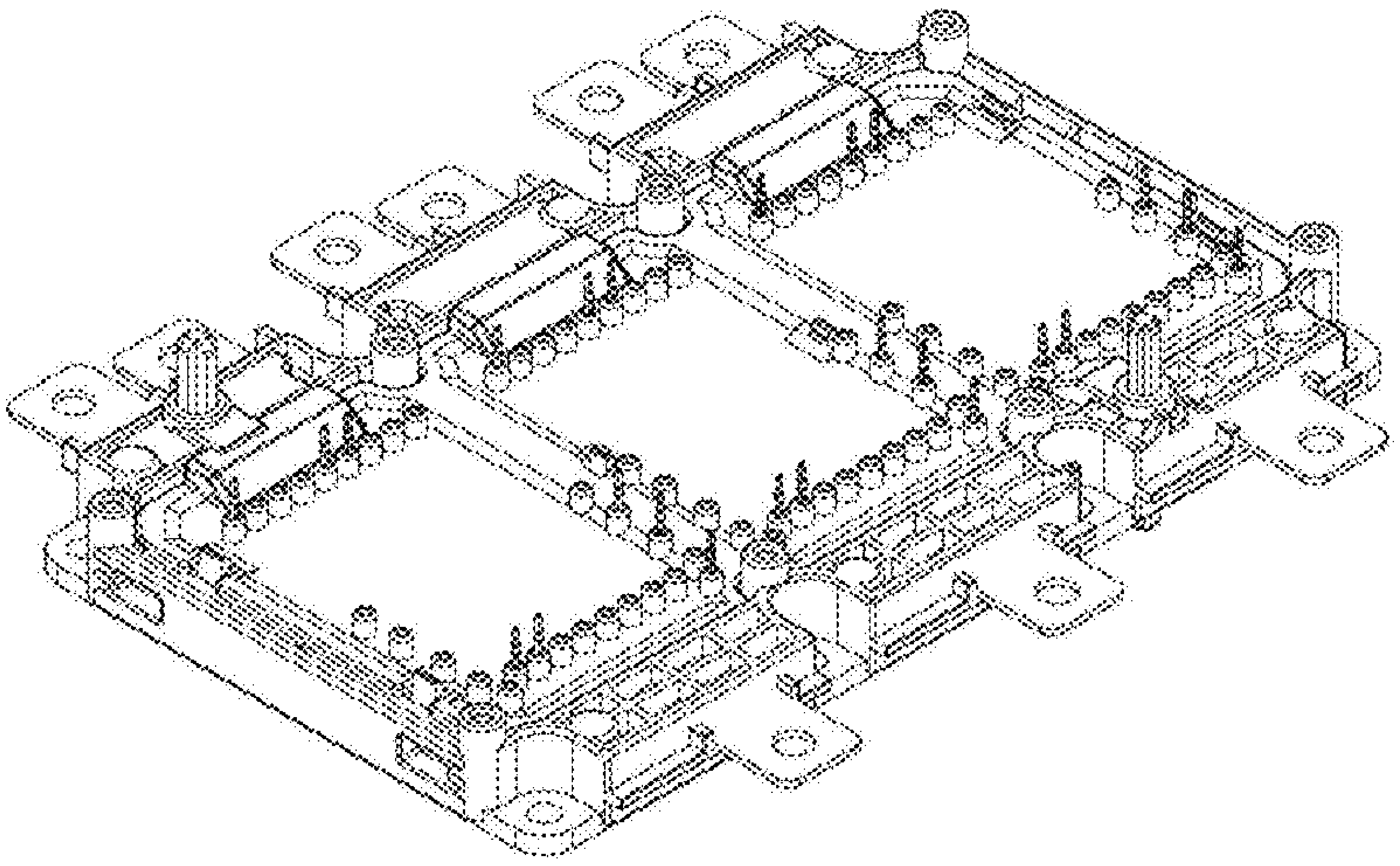
(57) **CLAIM**

The ornamental design for a power semiconductor module, as shown and described.

DESCRIPTION

FIG. **1** is a bottom plan view of a power semiconductor module showing our new design;
FIG. **2** is a top plan view thereof;
FIG. **3** is a side elevational view thereof;
FIG. **4** is another side elevational view thereof; and,
FIG. **5** is a top, side perspective view thereof.
All surfaces not shown form no part of the claimed design.

1 Claim, 5 Drawing Sheets



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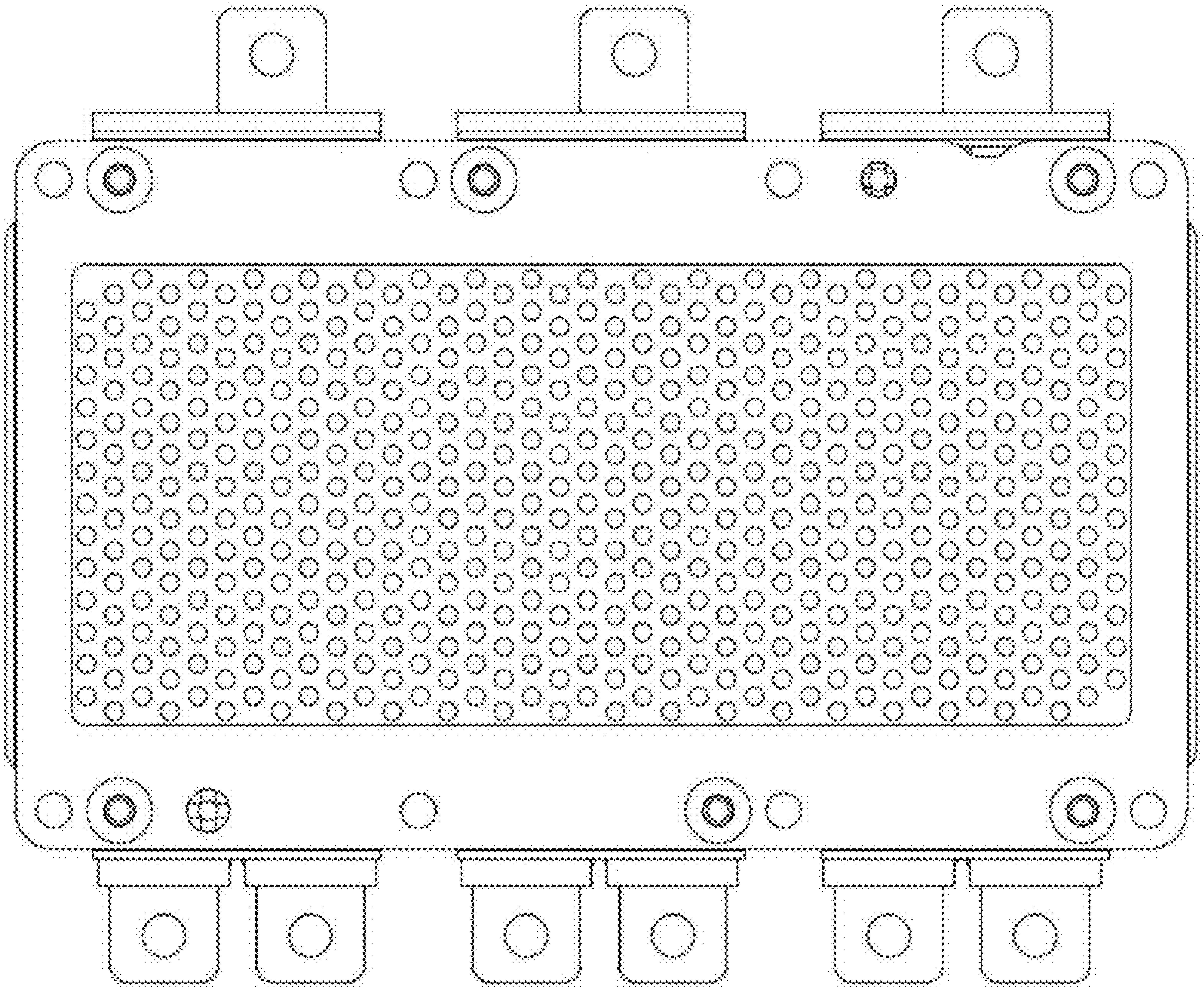

Figure 1

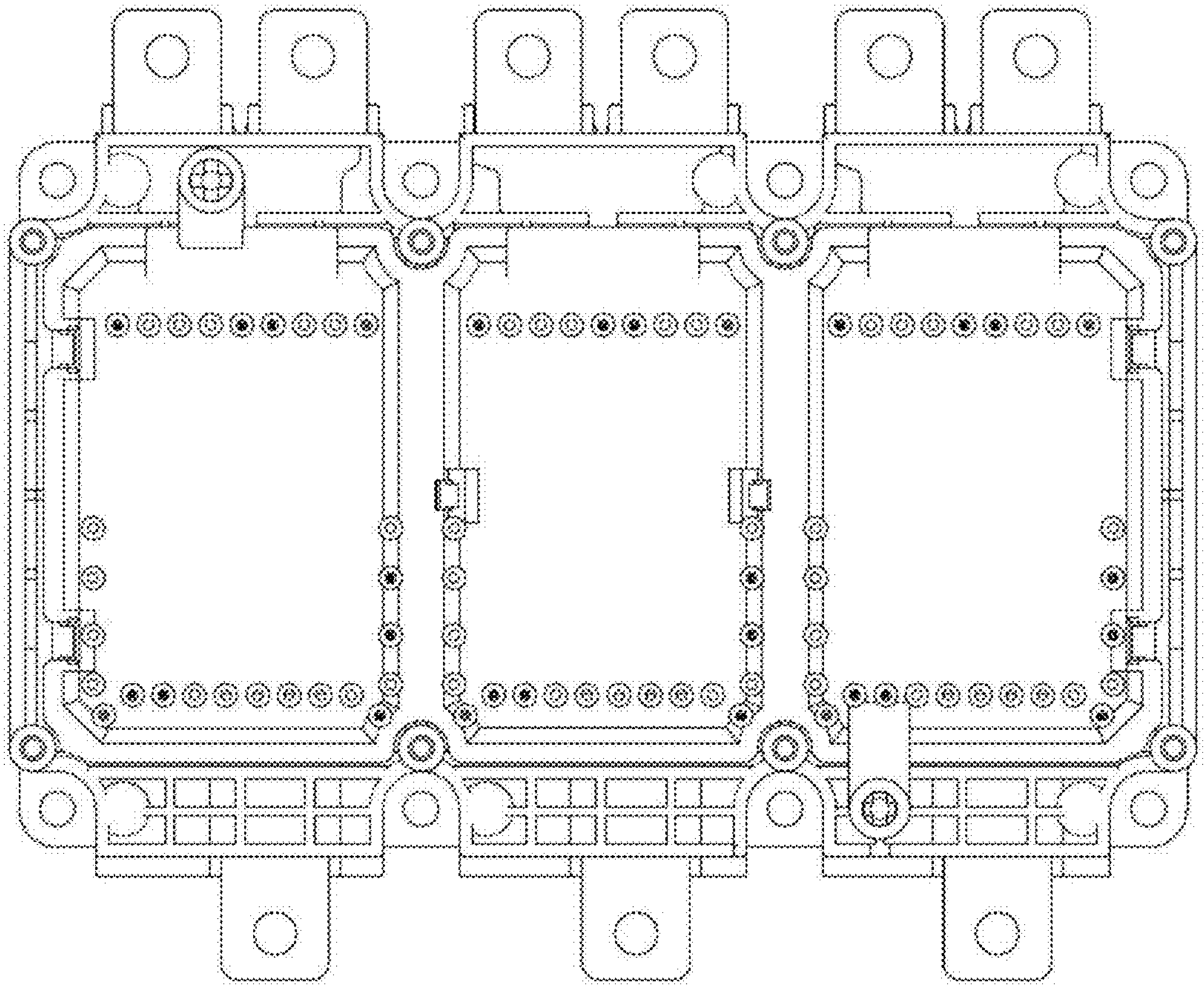

Figure 2

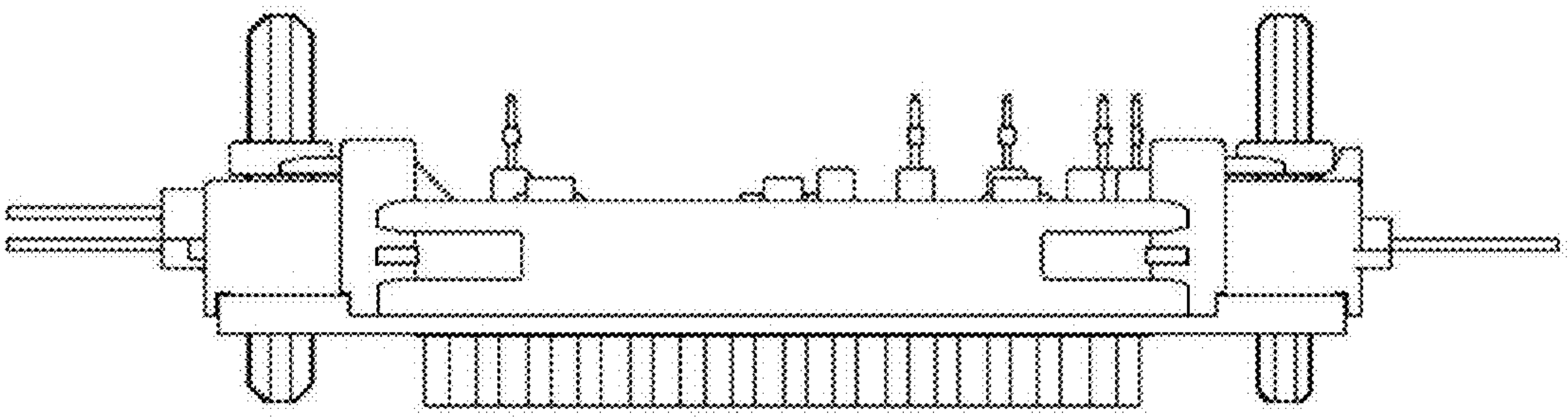

Figure 3

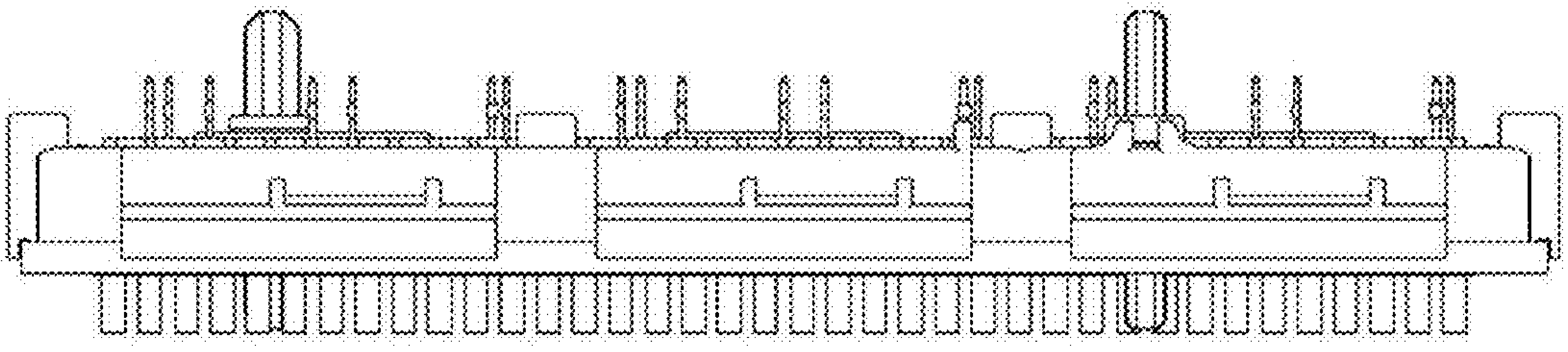

Figure 4

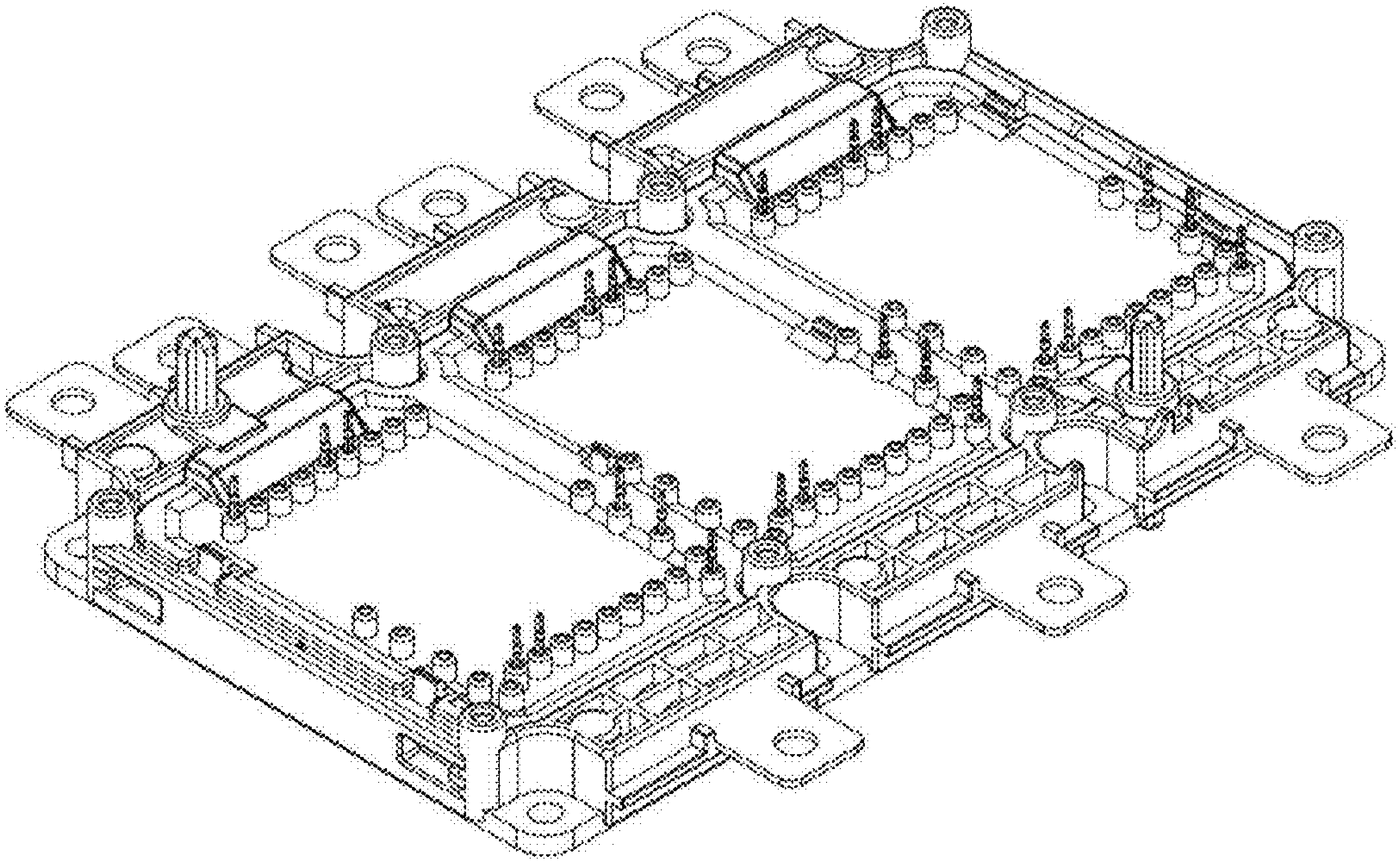

Figure 5